

## Evening Session 1

### PANEL DISCUSSION

#### AMORPHOUS AND POLYCRYSTALLINE SILICON

#### THIN FILM DEVICES

Chairman : Y.HAMAKAWA (Osaka Univ.)  
Panelists : J.J.HANAK (RCA, USA)  
                  Y.KUWANO (Sanyo)  
                  E.MARUYAMA (Hitachi)  
                  M.MATSUMURA (Tokyo Inst. Tech.)  
                  F.MORIN (CNET, France)  
                  I.SHIMIZU (Tokyo Inst. Tech.)

[alphabetic order]

Amorphous silicon (a-Si) is a very attractive material in many aspects for applications to various thin film devices such as solar cells, photosensors, imaging sensors and field-effect transistors. As the result of active and numerous research works, a-Si has now a bright and rosy future for these applications. In fact, some of them have been practically utilized and others have also been confirmed to be promising. Moreover, there are further possibilities of developing new applications of a-Si. Despite of good prospects of a-Si devices, we have still not fully solved problems of reliability and productivity.

Polycrystalline and microcrystalline silicon seem to complement the drawback in a-Si like as low mobility and small diffusion length, and to be possible to improve the performance of a-Si devices. However, it is necessary to establish the method how to control mixed structure of amorphous and poly-(or micro-) crystalline silicon.

All of participants of the Conference are welcome to join thorough and frank discussions on present status and problems, and future prospects of amorphous, microcrystalline and polycrystalline silicon devices including material aspect.

Coordinator : J.SHIRAFUJI (Osaka Univ.)

